NL3HS3124A

3.3 V, 2 Channel, 2:1 Differential Mux/Demux

The NL3HS3124A is a 2 channel, 2−to−1 differential multiplexer / demultiplexer for USB 3.0, PCI Express Generation 3, or other high−speed serial interface applications. The NL3HS3124A can switch two differential signals to one of two locations. The device has minimal channel−to−channel skew as well as minimal channel−to−channel crosstalk, making the device ideal for high−speed serial interface applications.

Features

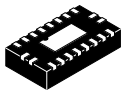
- 2 Bidirectional Channel, 2 : 1 Differential Multiplexer/Demultiplexer
- High−speed Signal Switching for 8 Gbps Applications
- High Bandwidth: > 6.3 GHz at −3 dB
- Low Insertion Loss:
  - −0.5 dB at 100 MHz
  - −2.8 dB at 4.0 GHz
- Low Return Loss: −9.27 dB at 4 GHz
- Low Crosstalk: −35 dB at 4 GHz
- Low Off−state Isolation: −19 dB at 4 GHz
- Low Intra−pair Skew: 5 ps Typical
- Low Inter−pair Skew: 35 ps Maximum
- V_{DD} Operating Range: 3.0 V to 3.6 V
- Shutdown Pin (SD) for Power−saving Mode
- Standby Current less than 1 μA
- ESD Tolerance:
  - 4000 V HBM
  - 300 V MM
  - 2000 V CDM
- 2.5 mm x 4.5 mm QFN20 Package
- This Device is Pb−Free, Halogen−Free/BFR−Free and is RoHS−Compliant

Applications

- Routing of High−speed Differential Signals
  - USB 3.0
  - PCIe Gen3
  - DisplayPort 1.2
  - SATA 6 Gbps

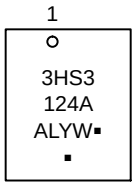
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QFN20
MN SUFFIX
CASE 485AA

MARKING DIAGRAM



3HS3124A = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NL3HS3124AMNTWG	QFN20 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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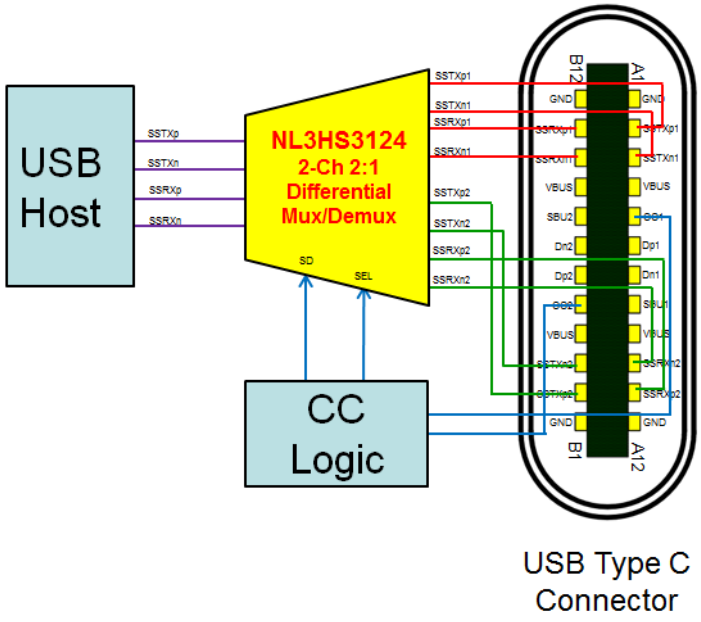


Figure 1. Typical Application

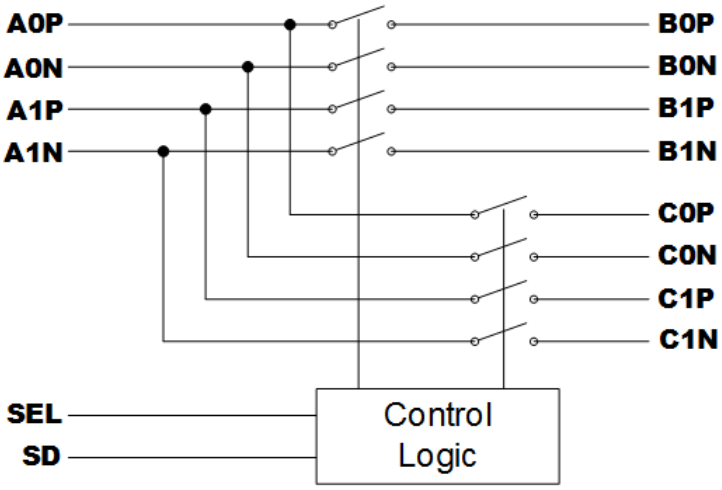


Figure 2. Block Diagram

Table 1. FUNCTION TABLE

SD	SEL	Function
L	L	An connected to Bn
L	H	An connected to Cn
H	X	An, Bn and Cn in Hi−Z, Device in Shutdown

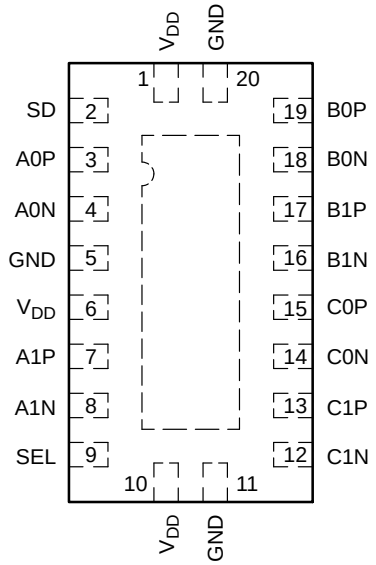


Figure 3. Pinout (Top Through View)

Table 2. PIN ASSIGNMENT

Pin Name	Pin	Type	Description
A0P	3	I/O	Channel 0, Port A Differential Signal I/O
A0N	4	I/O	
A1P	7	I/O	Channel 1, Port A Differential Signal I/O
A1N	8	I/O	
B0P	19	I/O	Channel 0, Port B Differential Signal I/O
B0N	18	I/O	
B1P	17	I/O	Channel 1, Port B Differential Signal I/O
B1N	16	I/O	
C0P	15	I/O	Channel 0, Port C Differential Signal I/O
C0N	14	I/O	
C1P	13	I/O	Channel 1, Port C Differential Signal I/O
C1N	12	I/O	
SEL	9	Input (CMOS)	Mux/Demux Select Pin
SD	2	Input (CMOS)	Shutdown Pin
V_{DD}	1, 6, 10	Power	Power
GND	5, 11, 20, Center Pad	Power	Ground

Table 3. MAXIMUM RATINGS

Symbol	Rating		Value	Unit
V_{DD}	Positive DC Supply Voltage		−0.5 to +4.6	V
V_{IN}	Digital Control Input Voltage (SEL, SD)		−0.5 to V_{DD}+0.5	V
T_S	Storage Temperature		−65 to +150	°C
ESD	ESD Performance			V
	HBM (JESD22−A114)	All Pins	4000	
	MM (JESD22−A115−A)	All Pins	300	
	CDM (JESD22−C101)	All Pins	2000	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 4. RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Typ	Max	Unit
V_{DD}	Positive DC Supply Voltage	3.0	3.3	3.6	V
V_{IN}	Digital Control Input Voltage (SEL, SD) (Note 1)	0		V_{DD}	V
V_{IS}	Differential Pin Input Voltage (An, Bn, Cn)	0		2.4	V
V_{IC}	Common−Mode Input Voltage (An, Bn, Cn)	0		2	V
V_{ID}	Differential Input Voltage (An, Bn, Cn), peak−to−peak	0		1.6	V
T_A	Operating Temperature	−40		85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

1. Control input must be held High or Low. It must not float.

Table 5. DC ELECTRICAL CHARACTERISTICS

Voltages referenced to GND. All typical values are at T_A = 25°C unless otherwise specified.

Symbol	Parameter	Conditions	V_{CC} (V)	T_A = −40°C to +85°C			Unit
				Min	Typ	Max	
V_{IH}	Input Voltage High	SEL, SD	3.0 – 3.6	2.0			V
V_{IL}	Input Voltage Low	SEL, SD	3.0 – 3.6			0.5	V
I_{IN}	Input Leakage Current	SEL, SD: V_{IN} = 0 V or V_{DD}	3.6			±5	μA
I_{IS}	Switch Input Leakage Current	An, Bn, Cn: V_{IS} = 0 V or 2.4 V	3.6			±10	μA
I_{DD}	Supply Current	Operating mode: SD = L	3.6		0.2	1	mA
		Shutdown mode: SD = H	3.6			1	μA

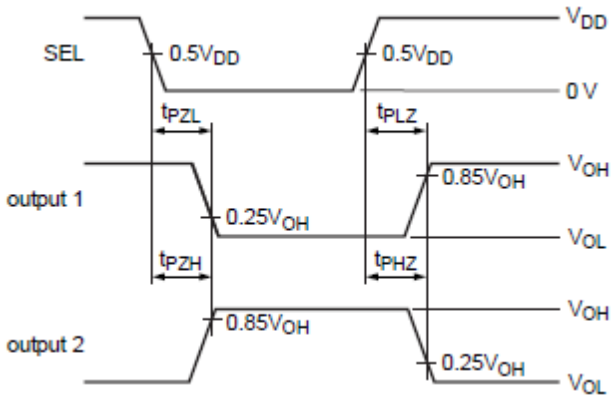
Table 6. DYNAMIC CHARACTERISTICS Voltages referenced to GND. All typical values are at T_A = 25°C unless otherwise specified.

Symbol	Parameter	Condition	V_{CC} (V)	T_A = −40°C to +85°C			Unit
				Min	Typ	Max	
DDIL	Differential Insertion Loss	Channel OFF	3.0 – 3.6				dB
		f = 4 GHz			−19		
		f = 100 MHz			−47		
		Channel ON					
		f = 4 GHz			−2.8		
		f = 100 MHz			−0.5		
DDNEXT	Differential Near−End Crosstalk	Adjacent Channels ON	3.0 – 3.6				dB
		f = 4 GHz			−26		
		f = 100 MHz			−62		
BW	−3 dB Bandwidth		3.0 – 3.6		6.3		GHz
DDRL	Differential Return Loss	f = 4 GHz	3.0 – 3.6		−9.27		dB
		f = 100 MHz			−23.2		
R_{ON}	Switch ON Resistance (Note 2)	VIS = 2 V, I_{IS} = 19 mA	3.3		6		Ω
$C_{IO(ON)}$	ON−State Input/Output Capacitance	f = 2.5 GHz	3.0 – 3.6		2.03		pF

2. Measured by the voltage drop between A and B pins at the indicated current through the switch. ON resistance is determined by the lower of the voltage on the two (A or B ports).

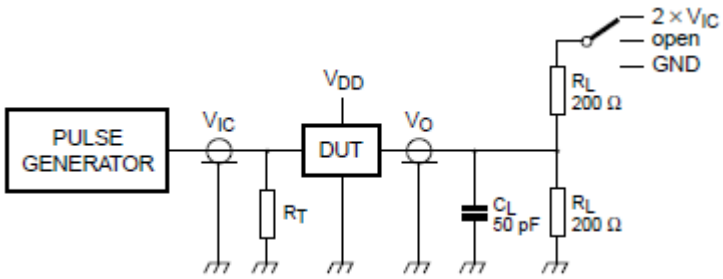
Table 7. SWITCHING CHARACTERISTICS All typical values are for V_{CC} = 3.3 V at T_A = 25°C unless otherwise specified.

Symbol	Parameter	Condition	V_{CC} (V)	T_A = −40°C to +85°C			Unit
				Min	Typ	Max	
$t_{STARTUP}$	Startup Time	Supply Voltage Valid, or SD going Low to channel specified operating conditions	3.0 – 3.6			10	ms
t_{PD}	Propagation Delay	Port A to Port B or C, or vice−versa	3.0 – 3.6		60		ps
t_{PZH}	OFF−State to High Propagation Delay		3.0 – 3.6			300	ns
t_{PZL}	OFF−State to Low Propagation Delay		3.0 – 3.6			70	ns
t_{PHZ}	High to OFF−State Propagation Delay		3.0 – 3.6			50	ns
t_{PLZ}	Low to OFF−State Propagation Delay		3.0 – 3.6			50	ns
$t_{sk(dif)}$	Differential Skew	Intra−pair	3.0 – 3.6		5		ps
t_{sk}	Skew	Inter−pair	3.0 – 3.6			35	ps



Output 1 is for an output with internal conditions such that the output is LOW except when disabled by the output control.
Output 2 is for an output with internal conditions such that the output is HIGH except when disabled by the output control.
The outputs are measured one at a time with one transition per measurement.

Figure 4. Voltage Waveforms, Enable and Disable Times



C_L = load capacitance; includes jig and probe capacitance.
R_T = termination resistance; should be equal to Z_o of the pulse generator.
All input pulses are supplied by generators having the following characteristics:
PRR ≤ 5 MHz; Z_o = 50 Ω; t_r ≤ 2.5 ns; t_f ≤ 2.5 ns.

Figure 5. Test Circuit for Switching Times

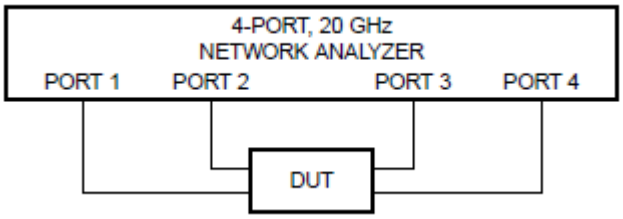


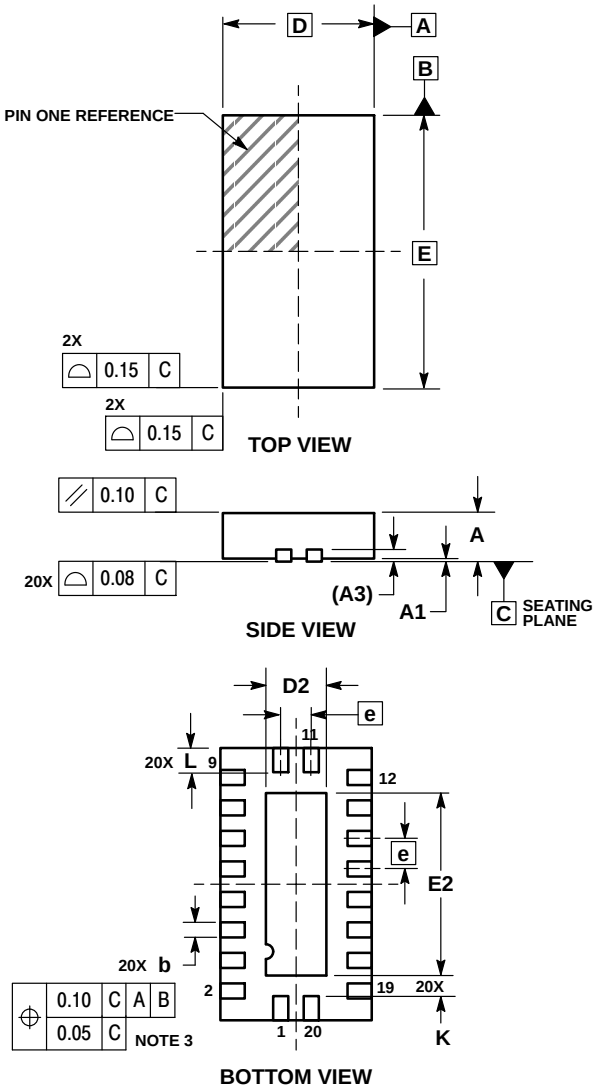
Figure 6. Test Circuit

Table 8. LOADING CONDITIONS FOR SWITCHING/TIMING TESTS

Test	Load		Switch
	C_L	R_L	
t_{PLZ}, t_{PZL} (Output on B Side)	50 pF	200 Ω	2 x V_{IC}
t_{PHZ}, t_{PZH} (Output on B Side)	50 pF	200 Ω	GND
t_{PD}		200 Ω	Open

PACKAGE DIMENSIONS

QFN20, 2.5x4.5 MM
CASE 485AA
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS	
DIM	MIN	MAX
A	0.80	1.00
A1	0.00	0.05
A3	0.20 REF	
b	0.20	0.30
D	2.50 BSC	
D2	0.85	1.15
E	4.50 BSC	
E2	2.85	3.15
e	0.50 BSC	
K	0.20	---
L	0.35	0.45

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